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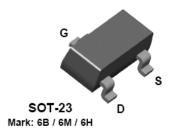
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February 2009

# 2N5484/5485/5486 MMBF5484/5485/5486





NOTE: Source & Drain are interchangeable

# **N-Channel RF Amplifier**

This device is designed primarily for electronic switching applications such as low On Resistance analog switching. Sourced from Process 50.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{DG}$	Drain-Gate Voltage	25	V
V <sub>GS</sub>	Gate-Source Voltage	- 25	V
I <sub>GF</sub>	Forward Gate Current	10	mA
T <sub>J</sub> ,T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

<u>NOTES:</u>
1) These ratings are based on a maximum junction temperature of 150 degrees C.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5484-5486	*MMBF5484-5486	
P <sub>D</sub>	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
R <sub>e</sub> Jc	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

<sup>2)</sup> These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

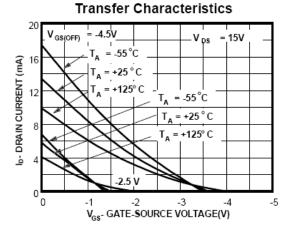
# N-Channel RF Amplifier (continued)

Cumbal	Parameter	Test Conditions	N1:	T	Mass	Units
Symbol	Parameter	rest Conditions	Min	Тур	Max	Units
OFF CHAI	RACTERISTICS					
V <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	I <sub>G</sub> = - 1.0 μA, V <sub>DS</sub> = 0	- 25			V
I <sub>GSS</sub>	Gate Reverse Current	V <sub>GS</sub> = - 20 V, V <sub>DS</sub> = 0			- 1.0	nA
V <sub>GS(off)</sub>	Gate-Source Cutoff Voltage	V <sub>GS</sub> = - 20 V, V <sub>DS</sub> = 0, T <sub>A</sub> = 100°C V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 nA <b>5484</b>	- 0.3		- 0.2	μA
v G5(011)	outo-source outon voltage	5485	- 0.5		- 4.0	V
ON CHAR	ACTERISTICS	5486	- 2.0		- 6.0	V
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current*	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 <b>5484</b>	1.0		5.0	mA
-500		5485	4.0		10	mA
		5486	8.0		20	mA
SMALL SI	GNAL CHARACTERISTICS Forward Transfer Conductance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 1.0 kHz	2000		0000	
		5484 5485	3000 3500		6000 7000	μmho μmho
		5486	4000		8000	μmho
Re(yis)	Input Conductance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 100 MHz 5484			100	μmho
		V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 400 MHz <b>5485 / 5486</b>			1000	μmho
gos	Output Conductance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$			50	
		5484 5485			60	μmho μmho
		5486			75	μmho
Re <sub>(yos)</sub>	Output Conductance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 100 MHz <b>5484</b>			75	μmho
		V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 400 MHz <b>5485 / 5486</b>			100	μmho
Re(yfs)	Forward Transconductance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 100 MHz			100	μππο
		<b>5484</b> V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 400 MHz	2500			μmho
		5485	3000			μmho
		5486	3500			μmho
Ciss	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ MHz}$			5.0	pF
Crss	Reverse Transfer Capacitance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 1.0 MHz			1.0	pF
Coss	Output Capacitance	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0, f = 1.0 MHz			2.0	pF
NF	Noise Figure	$V_{DS}$ = 15 V, $R_{G}$ = 1.0 k $\Omega$ , f = 100 MHz 5484			3.0	dB
		$V_{DS}$ = 15 V, $R_{G}$ = 1.0 k $\Omega$ , f = 400 MHz 5484		4.0		dB
		$V_{DS}$ = 15 V , $R_{G}$ = 1.0 k $\Omega$ , f = 100 MHz 5485 / 5486			2.0	dB
		$V_{DS}$ = 15 V, $R_{G}$ = 1.0 kΩ, f = 400 MHz 5485 / 5486			4.0	dB

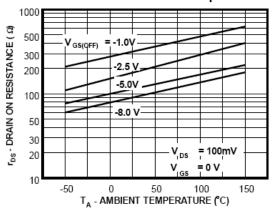
#### N-Channel RF Amplifier

(continued)

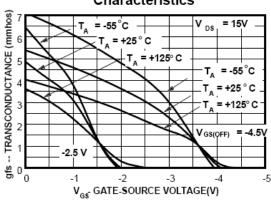
#### **Typical Characteristics**



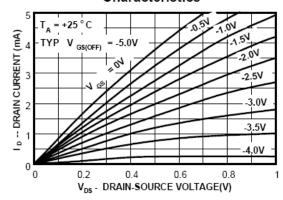
#### **Channel Resistance vs Temperature**



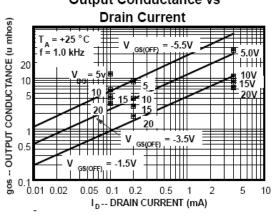
#### Transconductance Characteristics



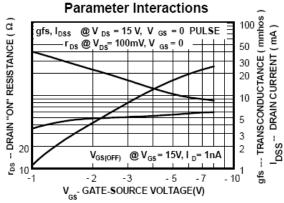
#### Common Drain-Source Characteristics



#### **Output Conductance vs**

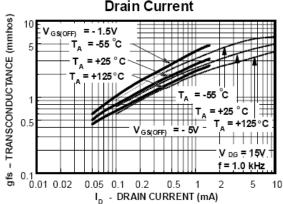


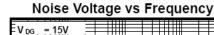
# Transconductance

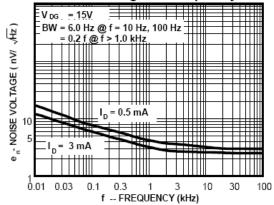


### Typical Characteristics (continued)

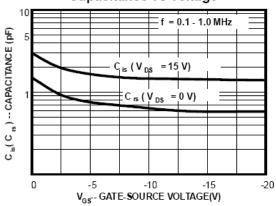
#### Transconductance vs **Drain Current**



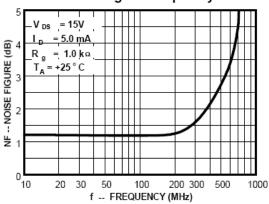




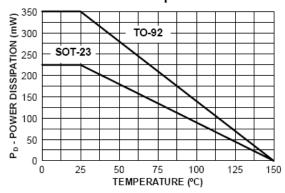
#### Capacitance vs Voltage



#### Noise Figure Frequency



#### Power Dissipation vs. **Ambient Temperature**

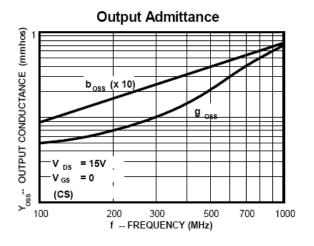


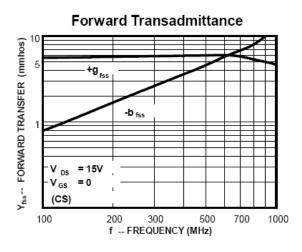
## N-Channel RF Amplifier

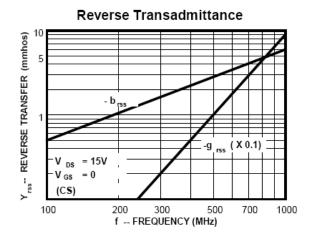
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#### **Common Source Characteristics**

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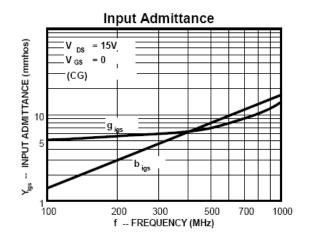


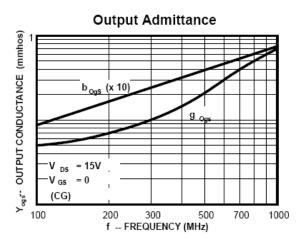


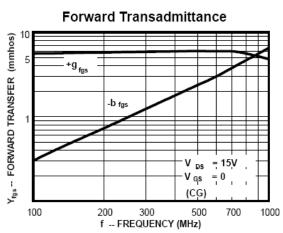
## **N-Channel RF Amplifier**

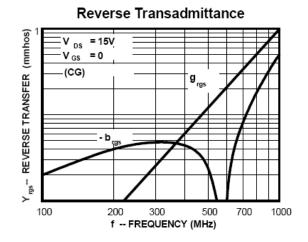
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### **Common Gate Characteristics**













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